

TS555

Low power single CMOS timer

Features

- Very low power consumption: 110 µA typ at V_{CC} = 5 V 90 µa typ at V_{CC} = 3 V
- High maximum astable frequency of 2.7 MHz
- Pin-to-pin functionally-compatible with bipolar NE555
- Wide voltage range: +2 V to +16 V
- Supply current spikes reduced during output transitions
- High input impedance: $10^{12} \Omega$
- Output compatible with TTL, CMOS and logic MOS

Description

The TS555 is a single CMOS timer with a very low consumption: ($I_{cc(TYP)}$ TS555 = 110 µA at V_{CC} = +5 V versus $I_{cc(TYP)}$ NE555 = 3 mA), and high frequency: ($f_{f(max.)}$ TS555 = 2.7 MHz versus $f_{(max)}$ NE555 = 0.1 MHz).

Timing remains accurate in both monostable and astable mode.

The TS555 provides reduced supply current spikes during output transitions, which enable the use of lower decoupling capacitors compared to those required by bipolar NE555.

With the high input impedance $(10^{12}\Omega)$, timing capacitors can also be minimized.



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Absolute maximum ratings and operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	+18	V
I _{OUT}	Output current	± 100	mA
R _{thja}	Thermal resistance junction to ambient DIP8 ⁽¹⁾ SO8 ⁽²⁾ TSSOP8 ⁽²⁾	85 125 120	°C/W
R _{thjc}	Thermal resistance junction to case DIP8 ⁽¹⁾ SO8 ⁽²⁾ TSSOP8 ⁽²⁾	41 40 37	°C/W
Тj	Junction temperature	+150	°C
T _{stg}	Storage temperature range	-65 to +150	°C
	Human body model (HBM) ⁽³⁾	1500	
ESD	Machine model (MM) ⁽⁴⁾	200	V
	Charged device model (CDM) ⁽⁵⁾	1000	

Table 1. Absolute maximum ratings

1. Short-circuits can cause excessive heating. These values are typical and specified for a single layer PCB.

2. Short-circuits can cause excessive heating. These values are typical and specified for a four layers PCB.

 Human body model: a 100 pF capacitor is charged to the specified voltage, then discharged through a 1.5kΩ resistor between two pins of the device. This is done for all couples of connected pin combinations while the other pins are floating.

4. Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω). This is done for all couples of connected pin combinations while the other pins remain floating.

5. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to the ground.

Table 2.	Operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	2 to 16	V
I _{OUT}	Output sink current Output source current	10 50	mA
T _{oper}	Operating free air temperature range TS555C TS555I TS555M	0 to +70 -40 to +125 -55 to +125	°C



2 Schematic diagrams











Table 3. Functions table

Reset	Trigger	Threshold	Output
Low	х	х	Low
High	Low	х	High
High	High	High	Low
High	High	Low	Previous state

Note:

LOW: level voltage \leq minimum voltage specified. HIGH: level voltage \geq maximum voltage specified. x: irrelevant.



3 Electrical characteristics

Table 4. Static electrical characteristics

$V_{CC} = +2 V, T_{amb} = +25^{\circ}$	C, Reset to V _{CC} (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply current (no load, high and low states) $T_{min.} \leq T_{amb} \leq T_{max}$		65	200 200	μΑ
V _{CL}	Control voltage level T _{min.} ≤T _{amb} ≤T _{max}	1.2 1.1	1.3	1.4 1.5	V
V _{DIS}	Discharge saturation voltage (I _{dis} = 1 mA) T _{min.} ≤T _{amb} ≤T _{max}		0.05	0.2 0.25	V
I _{DIS}	Discharge pin leakage current		1	100	nA
V _{OL}	Low level output voltage (I _{sink} = 1 mA) T _{min.} ≤T _{amb} ≤T _{max}		0.1	0.3 0.35	V
V _{OH}	High level output voltage (I _{source} = -0.3 mA) T _{min.} ≤T _{amb} ≤T _{max}	1.5 1.5	1.9		V
V _{TRIG}	Trigger voltage T _{min.} ≤T _{amb} ≤T _{max}	0.4 0.3	0.67	0.95 1.05	V
I _{TRIG}	Trigger current		10		pА
I _{TH}	Threshold current		10		pА
V _{RESET}	Reset voltage T _{min.} ≤T _{amb} ≤T _{max}	0.4 0.3	1.1	1.5 2.0	V
I _{RESET}	Reset current		10		pА



	$V_{CC} = +3 V$, $I_{amb} = +25^{\circ} C$, Reset to V_{CC}		other wis	se specifi	ieu)
Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply current (no load, high and low states) $T_{min.} \leq T_{amb} \leq T_{max}$		90	230 230	μA
V_{CL}	Control voltage level T _{min.} ≤T _{amb} ≤T _{max}	1.8 1.7	2	2.2 2.3	V
V _{DIS}	Discharge saturation voltage (I _{dis} = 1 mA) T _{min.} ≤T _{amb} ≤T _{max}		0.05	0.2 0.25	V
I _{DIS}	Discharge pin leakage current		1	100	nA
V _{OL}	Low level output voltage (I _{sink} = 1 mA) T _{min.} ≤T _{amb} ≤T _{max}		0.1	0.3 0.35	V
V _{OH}	High level output voltage (I _{source} = -0.3 mA) T _{min.} ≤T _{amb} ≤T _{max}	2.5 2.5	2.9		V
V _{TRIG}	Trigger voltage T _{min.} ≤T _{amb} ≤T _{max}	0.9 0.8	1	1.1 1.2	V
I _{TRIG}	Trigger current		10		pА
I _{TH}	Threshold current		10		pА
V _{RESET}	Reset voltage T _{min.} ≤T _{amb} ≤T _{max}	0.4 0.3	1.1	1.5 2.0	V
I _{RESET}	Reset current		10		pА

Table 5. Static electrical characteristics





Symbol	$v_{CC} = +3 v$, $r_{amb} = +23 v$, r_{eset} to v_{CC} Parameter	Min.	Тур.	Max.	, Unit
	Timing accuracy (monostable) ⁽¹⁾ $R = 10 k\Omega C = 0.1 \mu F$ $V_{CC} = 2 V$ $V_{CC} = 3 V$		1		%
	Timing shift with supply voltage variations (monostable) R = 10 k Ω C = 0.1 μ F, V _{CC} = 3 V ± 0.3 V ⁽¹⁾		0.5		%/V
	Timing shift with temperature ⁽¹⁾ $T_{min.} \leq T_{amb} \leq T_{max}.5$		75		ppm/°C
f _{max}	Maximum astable frequency $^{(2)}$ R _A = 470 Ω , R _B = 200 Ω , C = 200 pF		2		MHz
	Astable frequency accuracy $^{(2)}$ R_{A} = R_{B} = 1 k Ω to 100 k Ω C = 0.1 μF		5		%
	Timing shift with supply voltage variations (astable mode) $^{(2)}$ R _A = R _B = 1 k Ω to 100 k Ω C = 0.1 µF, V _{CC} = 3 to 5 V		0.5		%/V
^t R	Output rise time (C _{load} = 10 pF)		25		ns
tF	Output fall time (C _{load} = 10 pF)		20	-	ns
t _{PD}	Trigger propagation delay		100		ns
^t RPW	Minimum reset pulse width ($V_{trig} = 3 V$)		350		ns

Table 6.

Dynamic electrical characteristics $V_{CC} = +3 V$, $T_{amb} = +25^{\circ} C$, Reset to V_{CC} (unless otherwise specified)

1. See Figure 4.

2. See Figure 6.



Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply current (no load, high and low states) $T_{min.} \leq T_{amb} \leq T_{max}$		110	250 250	μA
V _{CL}	Control voltage level T _{min.} ≤T _{amb} ≤T _{max}	2.9 2.8	3.3	3.8 3.9	V
V_{DIS}	Discharge saturation voltage (I _{dis} = 10 mA) T _{min.} ≤T _{amb} ≤T _{max}		0.2	0.3 0.35	V
I _{DIS}	Discharge pin leakage current		1	100	nA
V _{OL}	Low level output voltage ($I_{sink} = 8 \text{ mA}$) T _{min.} $\leq T_{amb} \leq T_{max}$		0.3	0.6 0.8	V
V _{OH}	High level output voltage ($I_{source} = -2 \text{ mA}$) T _{min.} $\leq T_{amb} \leq T_{max}$	4.4 4.4	4.6		V
V _{TRIG}	Trigger voltage T _{min.} ≤T _{amb} ≤T _{max}	1.36 1.26	1.67	1.96 2.06	V
I _{TRIG}	Trigger current		10		pА
I _{TH}	Threshold current		10		pА
V _{RESET}	Reset voltage T _{min.} ≤T _{amb} ≤T _{max}	0.4 0.3	1.1	1.5 2.0	V
I _{RESET}	Reset current		10		pА

 Table 7.
 Static electrical characteristics

 V_{CC} = +5 V, T_{amb} = +25° C, Reset to V_{CC} (unless otherwise specified)



Symbol	Parameter	Min.	Тур.	Max.	Unit
	Timing accuracy (monostable) ⁽¹⁾ R = 10 k Ω C = 0.1 μ F		2		%
	Timing shift with supply voltage variations (monostable) ⁽¹⁾				
	R = 10 kΩ, C = 0.1 μ F,V _{CC} = 5 V ± 1 V		0.38		%/V
	Timing shift with temperature ⁽¹⁾ T _{min.} ≤T _{amb} ≤T _{max} 5		75		ppm/°C
f _{max}	Maximum astable frequency $^{(2)}$ R _A = 470 Ω R _B = 200 Ω C = 200 pF		2.7		MHz
	Astable frequency accuracy $^{(2)}$ R _A = R _B = 1 k Ω to 100 k Ω C = 0.1 μ F		3		%
	Timing shift with supply voltage variations (astable mode) ⁽²⁾				
	$R_A = R_B = 10 \text{ k}\Omega, C = 0.1 \mu\text{F}, V_{CC} = 5 \text{ to } 12 V$		0.1		%/V
^t R	Output rise time (C _{load} = 10 pF)		25		ns
tF	Output fall time (C _{load} = 10 pF)		20	-	ns
t _{PD}	Trigger propagation delay		100		ns
^t RPW	Minimum reset pulse width ($V_{trig} = 5 V$)		350		ns

Table 8.

Dynamic electrical characteristics $V_{CC} = +5 V$, $T_{amb} = +25^{\circ} C$, Reset to V_{CC} (unless otherwise specified)

1. See Figure 4.

2. See Figure 6.



	$v_{CC} = +12 v$, $r_{amb} = +23 c$, heset to v_{CC}			-	-
Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply current (no load, high and low states) $T_{min.} \leq T_{amb} \leq T_{max}$		170	400 400	μΑ
V _{CL}	Control voltage level T _{min.} ≤T _{amb} ≤T _{max}	7.4 7.3	8	8.6 8.7	V
V _{DIS}	Discharge saturation voltage (I _{dis} = 80 mA) T _{min.} ≤T _{amb} ≤T _{max}		0.09	1.5 2.0	V
I _{DIS}	Discharge pin leakage current		1	100	nA
V _{OL}	Low level output voltage (I _{sink} = 50 mA) T _{min.} ≤T _{amb} ≤T _{max}		1.2	2 2.8	V
V _{OH}	High level output voltage (I _{source} = -10 mA) T _{min.} ≤T _{amb} ≤T _{max}	10.5 10.5	11		V
V _{TRIG}	Trigger voltage T _{min.} ≤T _{amb} ≤T _{max}	3.2 3.1	4	4.8 4.9	V
I _{TRIG}	Trigger current		10		pА
I _{TH}	Threshold current		10		pА
V _{RESET}	Reset Voltage T _{min.} ≤T _{amb} ≤T _{max}	0.4 0.3	1.1	1.5 2.0	V
I _{RESET}	Reset current		10		pА

 Table 9.
 Static electrical characteristics

 V_{CC} = +12 V, T_{amb} = +25° C, Reset to V_{CC} (unless otherwise specified)

Table 10. Dynamic electrical characteristics V 10 V/T 05° C Paget to

V_{CC} = +12 V, T_{amb} = +25° C, Reset to V_{CC} (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Timing accuracy (monostable) $^{(1)}$ R = 10 k Ω C = 0.1 μ F, V _{CC} = +12 V		4		%
	Timing shift with supply voltage variations (monostable) $^{(1)}$ R = 10 k Ω C = 0.1 μ F, V _{CC} = +5 V ±1 V		0.38		%/V
	Timing shift with temperature $T_{min.} \leq T_{amb} \leq T_{max.}, V_{CC} = +5 V$		75		ppm/°C
f _{max}	Maximum astable frequency $^{(2)}$ R_A = 470 Ω R_B = 200 Ω C = 200 pF, V_{CC} = +5 V		2.7		MHz
	Astable frequency accuracy $R_A = R_B = 1 \ k\Omega$ to 100 k Ω C = 0.1 µF, V_{CC} = +12 V		3		%
	Timing shift with supply voltage variations (astable mode) $R_A = R_B = 1 \ k\Omega $ to 100 k Ω C = 0.1 µF, $V_{CC} = 5 $ to +12 V		0.1		%/V

1. See Figure 4.

2. See *Figure 6*.





Figure 3. Supply current (per timer) versus supply voltage



4 Application information

4.1 Monostable operation

In monostable mode, the timer operates like a one-shot generator. The external capacitor is initially held discharged by a transistor inside the timer, as shown in *Figure 4*.

Figure 4. Application schematic



The circuit triggers on a negative-going input signal when the level reaches $1/3 V_{CC}$. Once triggered, the circuit remains in this state until the set time has elapsed, even if it is triggered again during this interval. The duration of the output HIGH state is given by $t = 1.1 R \times C$.

Since the charge rate and threshold level of the comparator are both directly proportional to the supply voltage, the timing interval is independent of the supply. Applying a negative pulse simultaneously to the Reset terminal (pin 4) and the Trigger terminal (pin 2) during the timing cycle discharges the external capacitor and causes the cycle to start over. The timing cycle then starts on the positive edge of the reset pulse. While the reset pulse is applied, the output is driven to the LOW state.

When a negative trigger pulse is applied to pin 2, the flip-flop is set, releasing the short circuit across the external capacitor and driving the output HIGH. The voltage across the capacitor increases exponentially with the time constant $\tau = R \times C$.

When the voltage across the capacitor equals 2/3 V_{CC}, the comparator resets the flip-flop which then discharges the capacitor rapidly and drives the output to its LOW state. *Figure 5* shows the actual waveforms generated in this mode of operation.

When Reset is not used, it should be tied high to avoid any false triggering.



Figure 5. Timing diagram



4.2 Astable operation

When the circuit is connected as shown in *Figure 6* (pins 2 and 6 connected) it triggers itself and runs as a multi-vibrator. The external capacitor charges through R_A and R_B and discharges through R_B only. Therefore, the duty cycle may be precisely set by the ratio of these two resistors.

In the astable mode of operation, C charges and discharges between 1/3 V_{CC} and 2/3 V_{CC}. As in the triggered mode, the charge and discharge times, and therefore frequency, are independent of the supply voltage.

Figure 6. Application schematic



Figure 7 shows actual waveforms generated in this mode of operation.

The charge time (output HIGH) is given by:

 $t1 = 0.693 (R_A + R_B) C$

The discharge time (output LOW) by:

 $t2 = 0.693 \ x \ R_B \ x \ C$

Thus the total period T is given by:

$$T = t1 + t2 = 0.693 (R_A + 2R_B) C$$

The frequency of oscillation is then:

$$f = \frac{1}{T} = \frac{1.44}{(RA + 2RB)C}$$

The duty cycle is given by:

$$\mathsf{D} = \frac{\mathsf{R}\mathsf{B}}{\mathsf{R}\mathsf{A} + 2\mathsf{R}\mathsf{B}}$$

Figure 7. Timing diagram





5 Package information

In order to meet environmental requirements, STMicroelectronics offers these devices in ECOPACK[®] packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an STMicroelectronics trademark. ECOPACK specifications are available at: www.st.com.



TS555

5.1 DIP8 package information

Figure 8. DIP8 package mechanical drawing



Table 11. DIP8 package mechanical data

	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			5.33			0.210	
A1	0.38			0.015			
A2	2.92	3.30	4.95	0.115	0.130	0.195	
b	0.36	0.46	0.56	0.014	0.018	0.022	
b2	1.14	1.52	1.78	0.045	0.060	0.070	
С	0.20	0.25	0.36	0.008	0.010	0.014	
D	9.02	9.27	10.16	0.355	0.365	0.400	
E	7.62	7.87	8.26	0.300	0.310	0.325	
E1	6.10	6.35	7.11	0.240	0.250	0.280	
е		2.54			0.100		
eA		7.62			0.300		
eB			10.92			0.430	
L	2.92	3.30	3.81	0.115	0.130	0.150	



5.2 SO-8 package information





Table 12. SO-8 package mechanical data

	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.75			0.069	
A1	0.10		0.25	0.004		0.010	
A2	1.25			0.049			
b	0.28		0.48	0.011		0.019	
С	0.17		0.23	0.007		0.010	
D	4.80	4.90	5.00	0.189	0.193	0.197	
E	5.80	6.00	6.20	0.228	0.236	0.244	
E1	3.80	3.90	4.00	0.150	0.154	0.157	
е		1.27			0.050		
h	0.25		0.50	0.010		0.020	
L	0.40		1.27	0.016		0.050	
L1		1.04			0.040		
k	1 °		8°	1 °		8°	
ccc			0.10			0.004	



5.3 TSSOP8 package information

Figure 10. TSSOP8 package mechanical drawing



Table 13. TSSOP8 package mechanical data

	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.2			0.047	
A1	0.05		0.15	0.002		0.006	
A2	0.80	1.00	1.05	0.031	0.039	0.041	
b	0.19		0.30	0.007		0.012	
С	0.09		0.20	0.004		0.008	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	6.20	6.40	6.60	0.244	0.252	0.260	
E1	4.30	4.40	4.50	0.169	0.173	0.177	
е		0.65			0.0256		
k	0°		8°	0°		8°	
L	0.45	0.60	0.75	0.018	0.024	0.030	
L1		1			0.039		
aaa		0.1			0.004		



6 Ordering information

Order code	Temperature range	Package	Packaging	Marking
TS555CN		DIP8	Tube	TS555CN
TS555CD TS555CDT	0°C, +70°C	SO-8	Tube or Tape & reel	555C
TS555CPT		TSSOP8	Tape & reel	555C
TS555IN		DIP8	Tube	TS555IN
TS555ID TS555IDT	-40°C, +125°C	SO-8	Tube or Tape & reel	5551
TS555IPT		TSSOP8	Tape & reel	5551
TS555MN		DIP8	Tube	TS555CM
TS555MD TS555MDT	-55°C, +125°C	SO-8	Tube or Tape & reel	555M
TS555MPT		TSSOP8	Tape & reel	555M



7 Revision history

Table 15.	Document revision history
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Date	Revision	Changes
01-Feb-2003	1	Initial release.
03-Nov-2008	2	Document reformatted. Added output current, ESD and thermal resistance values in <i>Table 1: Absolute maximum ratings.</i> Added output current values in <i>Table 2: Operating conditions</i> .



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